

Andrey S Zubrilov

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2775997/publications.pdf>

Version: 2024-02-01

60
papers

763
citations

471061

17
h-index

552369

26
g-index

61
all docs

61
docs citations

61
times ranked

690
citing authors

#	ARTICLE	IF	CITATIONS
1	Hydride Vapor-Phase Epitaxy Reactor for Bulk GaN Growth. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 1900629.	0.8	8
2	Free-standing 2-inch bulk GaN crystal fabrication by HVPE using a carbon buffer layer. <i>Journal of Physics: Conference Series</i> , 2019, 1199, 012004.	0.3	2
3	Hydride vapor phase epitaxy reactor for bulk GaN growth. , 2019, , .		0
4	Laser slicing: A thin film lift-off method for GaN-on-GaN technology. <i>Results in Physics</i> , 2019, 13, 102233.	2.0	23
5	Thick GaN Film Stress-induced Self-separation. , 2019, , .		2
6	Laser Slicing, Process for GaN-on-GaN Technology. , 2019, , .		0
7	Reactor materials for high purity HVPE GaN growth: a thermodynamic analysis. <i>Journal of Physics: Conference Series</i> , 2019, 1410, 012004.	0.3	0
8	On the laser lift-off of lightly doped micrometer-thick n-GaN films from substrates via the absorption of IR radiation in sapphire. <i>Semiconductors</i> , 2017, 51, 115-121.	0.2	2
9	On the laser detachment of n-GaN films from substrates, based on the strong absorption of IR light by free charge carriers in n +GaN substrates. <i>Semiconductors</i> , 2016, 50, 699-704.	0.2	4
10	Two modes of HVPE growth of GaN and related macrodefects. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 468-471.	0.8	18
11	Nature of V-Shaped Defects in GaN. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JE14.	0.8	25
12	Effect of localized tail states in InGaN on the efficiency droop in GaN light-emitting diodes with increasing current density. <i>Semiconductors</i> , 2012, 46, 1032-1039.	0.2	10
13	Thick GaN Films Grown on Patterned Sapphire Substrates. <i>ECS Transactions</i> , 2011, 35, 91-97.	0.3	8
14	Effect of Growth Parameters on Stress in HVPE GaN Films. <i>ECS Transactions</i> , 2011, 35, 73-81.	0.3	2
15	On Application of Sublimation Epitaxy to Growth of Bulk 3C-SiC Crystals. <i>Materials Science Forum</i> , 2011, 679-680, 12-15.	0.3	1
16	Mechanism of the GaN LED efficiency falloff with increasing current. <i>Semiconductors</i> , 2010, 44, 794-800.	0.2	22
17	Use of sublimation epitaxy for obtaining volume 3C-SiC crystals. <i>Technical Physics Letters</i> , 2010, 36, 574-576.	0.2	0
18	Defect-related tunneling mechanism of efficiency droop in III-nitride light-emitting diodes. <i>Applied Physics Letters</i> , 2010, 96, 133502.	1.5	84

#	ARTICLE	IF	CITATIONS
19	Study of the 3C-SiC layers grown on the 15R-SiC substrates. Semiconductors, 2009, 43, 756-759.	0.2	3
20	Effect of the electric field on the intensity and spectrum of emission from InGaN/GaN quantum wells. Semiconductors, 2009, 43, 1499-1505.	0.2	3
21	ZnO/GaN heterostructure for LED applications. Journal of Modern Optics, 2009, 56, 653-660.	0.6	21
22	Investigation of n-GaN/p-SiC/n-SiC heterostructures. Journal of Crystal Growth, 2007, 300, 239-241.	0.7	8
23	White electroluminescence from ZnO/GaN structures. Semiconductors, 2007, 41, 564-569.	0.2	22
24	Luminescent properties of GaN-based epitaxial layers and heterostructures grown on porous SiC substrates. Technical Physics Letters, 2007, 33, 83-85.	0.2	2
25	Electrical Properties of n-GaN/p-SiC Heterojunctions. Semiconductors, 2005, 39, 1403.	0.2	1
26	Optical properties of GaN grown on Si (111) by gas source molecular beam epitaxy with ammonia. Journal of Applied Physics, 2002, 91, 1209-1212.	1.1	18
27	Properties of Si-Doped GaN Layers Grown by HVPE. Physica Status Solidi A, 2001, 188, 433-437.	1.7	15
28	Gas source molecular beam epitaxy of high quality Al _x Ga _{1-x} N (0 ≤ x ≤ 1) on Si(111). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1409.	1.6	21
29	Structural, electrical, and optical properties of low-doped 4H-SiC chemical vapor deposited epitaxial layers. Journal of Applied Physics, 2001, 90, 5402-5409.	1.1	11
30	High Quality AlN and GaN Grown on Si(111) by Gas Source Molecular Beam Epitaxy with Ammonia. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 467-473.	1.0	3
31	Growth of AlGaIn on Si(111) by gas source molecular beam epitaxy. Applied Physics Letters, 2000, 76, 3028-3030.	1.5	34
32	High-dose Al-implanted 4H-SiC p+-n-n+ junctions. Applied Physics Letters, 2000, 77, 3051-3053.	1.5	20
33	Growth of SiC and GaN on Porous Buffer Layers. Materials Science Forum, 2000, 338-342, 225-228.	0.3	6
34	Strain relaxation in GaN layers grown on porous GaN sublayers. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 1.	1.0	48
35	Insulating GaN:Zn layers grown by hydride vapor phase epitaxy on SiC substrates. Applied Physics Letters, 1999, 75, 3138-3140.	1.5	62
36	Optical properties of gallium nitride bulk crystals grown by chloride vapor phase epitaxy. Semiconductors, 1999, 33, 1067-1071.	0.2	13

#	ARTICLE	IF	CITATIONS
37	Properties and Effects of Hydrogen in GaN. Materials Research Society Symposia Proceedings, 1999, 595, 1.	0.1	2
38	GaN and AlN Layers Grown by Nano Epitaxial Lateral Overgrowth Technique on Porous Substrates. Materials Research Society Symposia Proceedings, 1999, 595, 1.	0.1	1
39	AlN Wafers Fabricated by Hydride Vapor Phase Epitaxy. Materials Research Society Symposia Proceedings, 1999, 595, 1.	0.1	6
40	High Quality AlN and GaN Grown on Si(111) by Gas Source Molecular Beam Epitaxy with Ammonia. Materials Research Society Symposia Proceedings, 1999, 595, 1.	0.1	1
41	Optically Transparent 6H-Silicon Carbide. Materials Science Forum, 1998, 264-268, 53-56.	0.3	0
42	Gas source molecular beam epitaxy of GaN with hydrazine on spinel substrates. Applied Physics Letters, 1998, 72, 2361-2363.	1.5	7
43	Crystal Structure and Optical Properties of Bulk GaN Crystals Grown from a Melt at Reduced Pressure. Materials Science Forum, 1998, 264-268, 1331-1334.	0.3	3
44	GaN/GaAs(111)B grown by molecular beam epitaxy using hydrazine. , 1997, , .		0
45	AlN/GaN and AlGaIn/GaN Heterostructures Grown by HVPE on SiC Substrates. Materials Research Society Symposia Proceedings, 1997, 482, 329.	0.1	12
46	Optical confinement and threshold currents in III-V nitride heterostructures: Simulation. Journal of Applied Physics, 1997, 81, 2952-2956.	1.1	20
47	Waveguide properties of gallium, aluminum, and indium nitride heterostructures. Semiconductors, 1997, 31, 51-54.	0.2	0
48	Effect of ion doping on the electrical and luminescent properties of 4H-SiC epitaxial p-n junctions. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 46, 259-262.	1.7	4
49	Luminescence properties of gallium nitride layers grown on silicon carbide substrates by gas-phase epitaxy in a chloride system. Semiconductors, 1997, 31, 523.	0.2	5
50	GaN Layers Grown by HVPE on P-type 6H-SiC Substrates. MRS Internet Journal of Nitride Semiconductor Research, 1996, 1, 1.	1.0	6
51	Recent progress in AlGaIn/GaN laser structures on 6H-SiC. , 1996, , .		0
52	Growth and characterization of GaN layers on SiC substrates. Journal of Crystal Growth, 1996, 166, 601-606.	0.7	9
53	Optical Properties of Nitride-based Structures Grown on 6H-SiC. MRS Internet Journal of Nitride Semiconductor Research, 1996, 1, 1.	1.0	10
54	Deep centers and electroluminescence in 4H-SiC diodes with a p-type base region. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 29, 181-184.	1.7	36

#	ARTICLE	IF	CITATIONS
55	AlGaN pn junctions. Applied Physics Letters, 1995, 67, 115-117.	1.5	17
56	Spontaneous and stimulated emission from photopumped GaN grown on SiC. Applied Physics Letters, 1995, 67, 533-535.	1.5	98
57	Picosecond time-resolved reflectivity of porous silicon. Optics Communications, 1994, 106, 65-68.	1.0	4
58	Recent progress in GaN/SiC LEDs and photopumped lasers. , 0, , .		0
59	6H- and 4H-silicon carbide for device applications. , 0, , .		0
60	Electrical and optical properties of Mg ion implanted GaN p-n junctions. , 0, , .		0